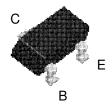


FSB660 / FSB660A



SuperSOT[™]-3 (SOT-23)

PNP Low Saturation Transistor

These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous.

Absolute Maximum Ratings* T_{A = 25°C unless otherwise noted}

Symbol	Parameter	FSB660/FSB660A	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	2	Α
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 °C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics $T_{A=25^{\circ}\text{C unless otherwise noted}}$

Symbol	Characteristic	Max	Units
		FSB660/FSB660A	
P _D	Total Device Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W

	PNP	Low :	Saturation	Transistor
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(continued)

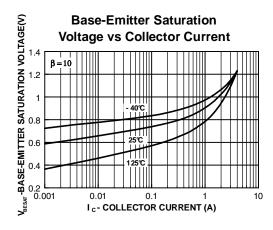
Electrical Characteristics

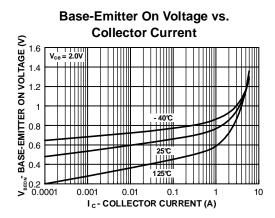
T_{A = 25°C} unless otherwise noted

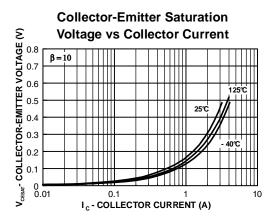
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	60		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA	60		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA	5		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 30 V		100	nA
		V _{CB} = 30 V, T _A =100°C		10	uA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V		100	nA
	A OTERIOTION:			l	
	ACTERISTICS* DC Current Gain	1 100 4 1/ 0 1/	70		_
h _{FE}	Do carront dam	I _C = 100 mA, V _{CE} = 2 V	100	300	
		I _C =500mA, V _{CE} =2V FSB660 FSB660A	250	550	
		I _C = 1 A, V _{CE} = 2 V	80		
		I _C = 1 A, V _{CE} = 2 V I _C = 2 A, V _{CE} = 2 V	40		
	Collector-Emitter Saturation Voltage			300	mV
V _{CE(sat)}	Collector-Enlitter Saturation Voltage	I _C = 1 A, I _B = 100 mA			IIIV
		I _C = 2 A, I _B =200 mA FSB660		350	
	Dana Fraittey Catawatian Valtage	FSB660A		300	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		1.25	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 2 V		1	V
SMALL SI	GNAL CHARACTERISTICS				
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1MHz		30	pF
f _T	Transition Frequency	I _C = 100 mA,V _{CE} = 5 V, f=100MHz	75		-

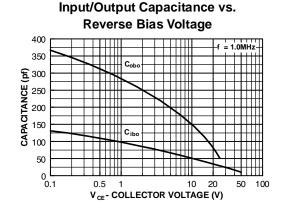
*Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

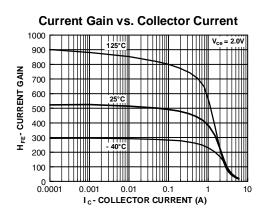
Typical Characteristics











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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. H3